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# **BTA10 and BTB10 Series**

10A TRIACs

SNUBBERLESS™ & STANDARD

**Table 1: Main Features** 

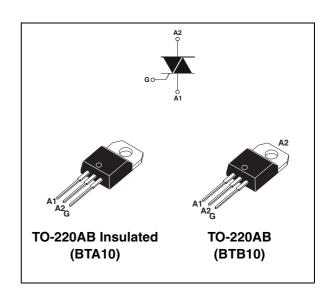
Symbol	Value	Unit
I <sub>T(RMS)</sub>	10	Α
V <sub>DRM</sub> /V <sub>RRM</sub>	600 and 800	V
I <sub>GT (Q₁)</sub>	25 to 50	mA

#### **DESCRIPTION**

Available either in through-hole or surface-mount packages, the **BTA10** and **BTB10** triac series is suitable for general purpose AC switching. They can be used as an ON/OFF function in applications such as static relays, heating regulation, induction motor starting circuits... or for phase control operation in light dimmers, motor speed controllers,...

The snubberless version (W suffix) is specially recommended for use on inductive loads, thanks to their high commutation performances.

By using an internal ceramic pad, the BTA series provides voltage insulated tab (rated at 2500V<sub>RMS</sub>) complying with UL standards (File ref.: E81734).



**Table 2: Order Codes** 

Part Number	Marking
BTA10-xxxxxRG	See page table 8 on
BTB10-xxxxxRG	page 6

**Table 3: Absolute Maximum Ratings** 

Symbol	Paramet	Value	Unit		
I,	RMS on-state current (full sine wave)	TO-220AB	$T_c = 105^{\circ}C$	10	Α
IT(RMS)		TO-220AB Ins.	$T_c = 95^{\circ}C$	10	Α
I <sub>TSM</sub>	Non repetitive surge peak on-state	F = 50 Hz	t = 20 ms	100	Α
TSM	current (full cycle, $T_j$ initial = 25°C)	F = 60 Hz	t = 16.7 ms	105	^
l <sup>2</sup> t	I <sup>2</sup> t Value for fusing	t <sub>p</sub> = 10 ms		55	A <sup>2</sup> s
dI/dt	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$ , $t_r \le 100 \text{ ns}$	F = 120 Hz	T <sub>j</sub> = 125°C	50	A/µs
V <sub>DSM</sub> /V <sub>RSM</sub>	Non repetitive surge peak off-state voltage	t <sub>p</sub> = 10 ms	T <sub>j</sub> = 25°C	V <sub>DSM</sub> /V <sub>RSM</sub> + 100	V
I <sub>GM</sub>	Peak gate current $t_p = 20 \mu s$ $T_j = 125^{\circ}C$		4	Α	
P <sub>G(AV)</sub>	Average gate power dissipation $T_j = 125^{\circ}C$			1	W
T <sub>stg</sub> T <sub>j</sub>	Storage junction temperature range Operating junction temperature range			- 40 to + 150 - 40 to + 125	°C

**Tables 4: Electrical Characteristics** ( $T_j = 25$ °C, unless otherwise specified)

# ■ SNUBBERLESS (3 quadrants)

Symbol Test Conditions		Quadrant		BTA10 / BTB10		Unit
		Quaurant		CW	BW	Oill
I <sub>GT</sub> (1)	$V_D = 12 \text{ V } R_1 = 33 \Omega$	1 - 11 - 111	MAX.	35	50	mA
V <sub>GT</sub>	VD = 12 V 11L = 30 32	1 - 11 - 111	MAX.	1.	.3	V
$V_{GD}$	$V_D = V_{DRM}$ $R_L = 3.3 \text{ k}\Omega$ $T_j = 125^{\circ}\text{C}$	1 - 11 - 111	MIN.	0.2		V
I <sub>H</sub> (2)	I <sub>T</sub> = 500 mA		MAX.	35	50	mA
l <sub>l</sub>	I <sub>G</sub> = 1.2 I <sub>GT</sub>	1 - 111	MAX.	50	70	mA
'L	'L 'G - 1.2 'G		IVIAX.	60	80	
dV/dt (2)	$V_D = 67 \text{ %}V_{DRM} \text{ gate open } T_j = 125 \text{°C}$		MIN.	500	1000	V/µs
(dl/dt)c (2)	Without snubber $T_j = 125$ °C		MIN.	5.5	9.0	A/ms

## ■ Standard (4 quadrants)

Symbol	Symbol Test Conditions			BTA10 / BTB10		Unit
Symbol				С	В	Oilit
I <sub>GT</sub> (1)		I - II - III	MAX.	25	50	mA
·GI (·/	$V_D = 12 V$ $R_L = 33 \Omega$	IV	WIAX.	50	100	ША
V <sub>GT</sub>		ALL	MAX.	1.	.3	<b>V</b>
$V_{GD}$	$V_D = V_{DRM}$ $R_L = 3.3 \text{ k}\Omega$ $T_j = 125^{\circ}\text{C}$ ALL		MIN.	0.2		٧
I <sub>H</sub> (2)	I <sub>T</sub> = 500 mA		MAX.	25	50	mA
I <sub>I</sub>	I <sub>G</sub> = 1.2 I <sub>GT</sub>	I - III - IV	MAX.	40	50	mA
'L 'G - ''- 'GT		=	WIAX.	80	100	IIIA
dV/dt (2)	$V_D = 67 \% V_{DRM}$ gate open $T_j = 125 ^{\circ}C$		MIN.	200	400	V/µs
(dV/dt)c (2)	$(dI/dt)c = 4.4 \text{ A/ms}$ $T_j = 125^{\circ}$	C	MIN.	5	10	V/µs

**Table 5: Static Characteristics** 

Symbol	Test Conditions			Value	Unit
V <sub>T</sub> (2)	$I_{TM} = 14 \text{ A}$ $t_p = 380  \mu\text{s}$	T <sub>j</sub> = 25°C	MAX.	1.55	V
V <sub>t0</sub> (2)	Threshold voltage	T <sub>j</sub> = 125°C	MAX.	0.85	V
R <sub>d</sub> (2)	Dynamic resistance	T <sub>j</sub> = 125°C	MAX.	40	mΩ
I <sub>DRM</sub>	$V_{DRM} = V_{RRM}$	T <sub>j</sub> = 25°C	MAX.	5	μA
I <sub>RRM</sub>	*DHM — *HHM	T <sub>j</sub> = 125°C	IVIAA.	1	mA

Note 1: minimum  $I_{GT}$  is guaranted at 5% of  $I_{GT}$  max. Note 2: for both polarities of A2 referenced to A1.

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**Table 6: Thermal resistance** 

Symbol	Parameter		Value	Unit
D	lunation to coop (AC)	TO-220AB	1.5	°C/W
R <sub>th(j-c)</sub> Junction to case (AC)	TO-220AB Insulated	2.4	- C/VV	
D	lunation to ambient	TO-220AB	60	°C/W
R <sub>th(j-a)</sub> Junction to ambient	TO-220AB Insulated	60	C/VV	

Figure 1: Maximum power dissipation versus RMS on-state current (full cycle)

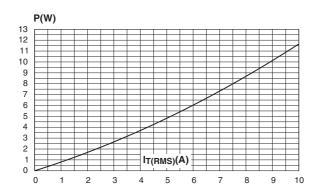


Figure 3: Relative variation of thermal impedance versus pulse duration

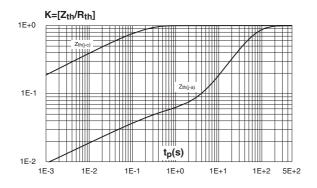


Figure 2: RMS on-state current versus case temperature (full cycle)

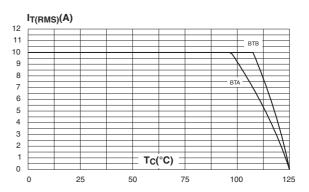
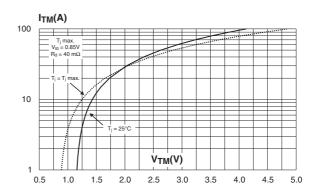


Figure 4: On-state characteristics (maximum values)



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Figure 5: Surge peak on-state current versus number of cycles

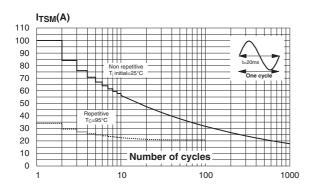


Figure 7: Relative variation of gate trigger current, holding current and latching current versus junction temperature (typical values)

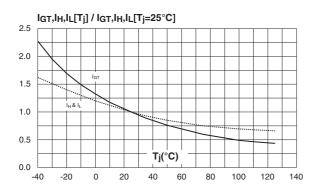


Figure 9: Relative variation of critical rate of decrease of main current versus junction temperature

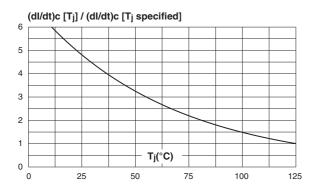


Figure 6: Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 10 \text{ ms}$  and corresponding value of  $l^2t$ 

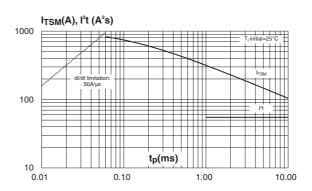
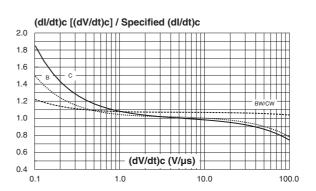
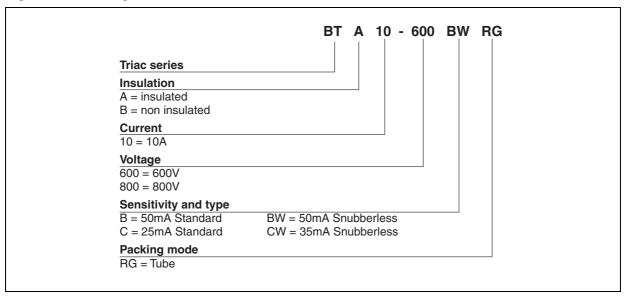


Figure 8: Relative variation of critical rate of decrease of main current versus (dV/dt)c (typical values)



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Figure 10: Ordering Information Scheme



**Table 7: Product Selector** 

Part Number	Voltag	e (xxx)	Sensitivity	Туре	
r art Number	600 V	800 V	Sensitivity	Турс	Package
BTA/BTB10-xxxB	Х	Х	50 mA	Standard	TO-220AB
BTA/BTB10-xxxBW	Х	Х	50 mA	Snubberless	TO-220AB
BTA/BTB10-xxxC	Х	Х	25 mA	Standard	TO-220AB
BTA/BTB10-xxxCW	Х	Х	35 mA	Snubberless	TO-220AB

BTB: non insulated TO-220AB package

DIMENSIONS REF. Millimeters Inches Min. Тур. Max. Min. Typ. Max. 15.20 15.90 0.598 0.625 Α В a1 3.75 0.147 Ø١ a2 13.00 14.00 0.511 0.551 Ĺ В 10.00 10.40 0.393 0.409 0.61 0.88 0.024 0.034 b1 b2 1.23 1.32 0.048 0.051 14 С 4.40 4.60 0.173 0.181 13 c1 0.49 0.70 0.019 0.027 c2 a1 2.72 0.094 c2 2.40 0.107 2.40 2.70 0.094 0.106 е a2 6.20 6.60 0.244 0.259 F ØI 3.75 3.85 0.147 0.151 14 15.80 16.40 16.80 0.622 0.646 0.661 L 2.65 2.95 0.104 0.116 12 1.14 1.70 0.044 0.066 0.044 13 1.14 1.70 0.066 М 2.60 0.102

Figure 11: TO-220AB (insulated and non insulated) Package Mechanical Data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: <a href="https://www.st.com">www.st.com</a>.

**Table 8: Ordering Information** 

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
BTA/BTB10-xxxyzRG	BTA/BTB10-xxxyz	TO-220AB	2.3 g	50	Tube

**Note:** xxx = voltage, yy = sensitivity, z = type

**Table 9: Revision History** 

Date	Revision	Description of Changes
Apr-2002	5A	Last update.
13-Feb-2006	6	TO-220AB delivery mode changed from bulk to tube. ECOPACK statement added.

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